

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
13 October 2005 (13.10.2005)

PCT

(10) International Publication Number
WO 2005/096380 A1

(51) International Patent Classification⁷: **H01L 27/10,**
45/00, G06K 19/07

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(21) International Application Number:
PCT/JP2005/006713

(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(22) International Filing Date: 30 March 2005 (30.03.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2004-110508 2 April 2004 (02.04.2004) JP

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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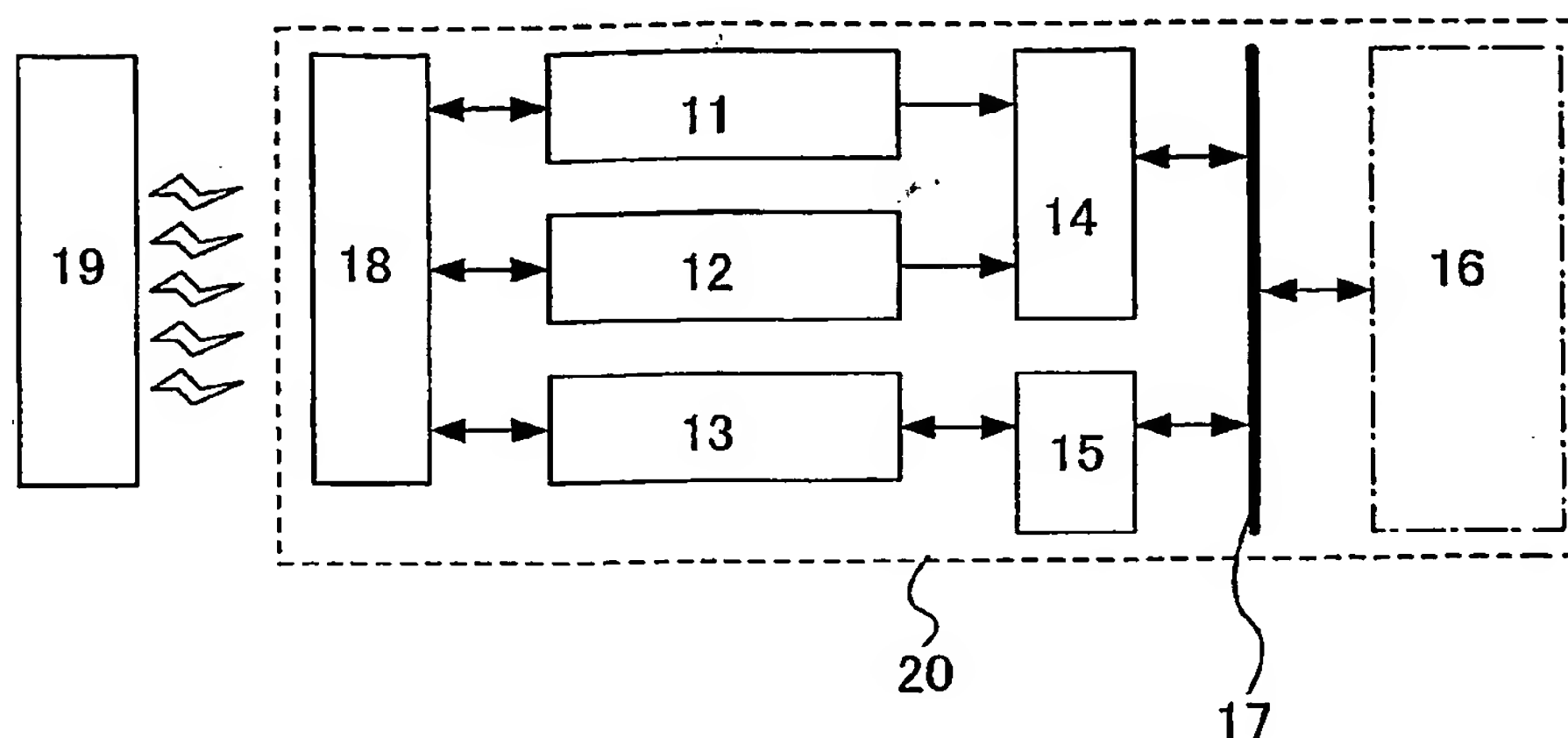
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Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: SEMICONDUCTOR DEVICE AND DRIVING METHOD OF THE SAME



(57) Abstract: The invention provides a semiconductor device including a memory of a simple structure to provide an inexpensive semiconductor device and a driving method thereof. The semiconductor device of the invention includes a phase change memory including a memory cell array having a plurality of memory cells, a control circuit that controls the phase change memory, and an antenna. The memory cell array includes a plurality of bit lines that extend in a first direction and word lines that extend in a second direction perpendicular to the first direction. Each of the plurality of memory cells includes a phase change layer provided between the bit lines and the word lines. In the semiconductor device having the aforementioned structure, one or both of a conductive layer that forms the bit lines and a conductive layer that forms the word lines transmits light.

WO 2005/096380 A1